

- Photovoltaics: 태양광 에너지
- Net solar power input to the earth is more than 10,000times humanity's current rate of use of fossil and nuclear fuels
- Photo: Greek word for light
- Volta: Italian inventor of battery, Alessandro Volta

- PV effect by Becquerel in 1839: wet cell battery with silver plates
- PV effect on solid selenium by Adams & Day from Cambridge in 1877
- Selenium + gold wire + glass by Fritts in 1883 with 1% efficiency

- PV effect in silicon (semiconductor) in 1953: 6% efficiency
- Single cell (1.5 watt) – Module – Array
- Efficiency in single Si cell: 17% (commercial), 24% (lab)

- Types of photovoltaics:

- (1) Monocrystalline silicon

- (2) Polycrystalline silicon

- (3) Silicon ribbons and sheets

- (4) Gallium arsenide

- (5) Thin film PV:

a-Si (amorphous silicon),

CIS (Copper Indium Diselenide,  $\text{CuInSe}_2$ ),

CIGS(Copper Indium Gallium Diselenide),

CdTe(Cadmium Telluride, CdTe)

- (6) Other type:

Multi-junction PV cells,

Silicon spheres,

Photoelectrochemical cells,

Third generation with nano technology

- Principles of semiconductor:
- crystalline Si, impurity (doping process), p-n junction
- n-type: silicon + phosphorus (surplus of free electrons)
- p-type: silicon + boron (deficit of free electrons)
- PV effect: photons, depletion region

Reducing cost: Polycrystalline silicon (but effc. 14%)  
(cf) polycrystalline films on ceramic or glass  
(by Pacific Solar, Astropower): effc. 10%

Raising efficiency: Gallium arsenide (GaAs)

-High light absorption coeff. BUT expensive

-Operate at relatively high temp. → space etc.

## Thin film PV: a-Si (amorphous silicon)

- Gas with silicon & hydrogen (e.g. silane:  $\text{SiH}_4$ ) & dopant by electric.
- p-i-n junction
- thinner, high absorp., process at lower temp. & cheaper, BUT low effc. as 12%  $\rightarrow$  4~8% (a few months)
- used at calculator

## Thin film PV: other types

- CIS (Copper Indium diselenide:  $\text{CuInSe}_2$ )
- CIGS (Copper Indium Gallium Diselenide)
  - effc. 17% at lab, 10% stable by Shell Solar, Würth Solar
- CdTe (Cadium Telluride)
  - Inexpensive process
  - effc. 10%

Silicon spheres  
by Texas Instruments

-Polycrystalline Si embedded  
between thin Al sheets

-Cheaper with low-grade Si

-Used at 20MWp plant by  
Automation Tooling Systems Inc.

## Cell – Module – Array

- Cell size: 1 – 15 cm, 1 -2 watts
- Standard module: 36 solar cells, 60 Wp (0.5m x 1.0m, 0.33m x 1.33m)
- Cleaning of module: reduction of effc. 4 %,  
→ thus req. over 20° inclination

Satellite solar power

Full 1365 W/m<sup>2</sup>

(cf) max 1000 W/m<sup>2</sup> at the earth

## Reducing the cost?

- If production at 500 MWp per year → \$1 per peak watt
- BoS (Balance of System) cost about  $\frac{3}{4}$  of module cost at present  
→ Should be below \$1 per watt
- effc. 17% → 24% at next decade (by Sharp Corporation)
- payback time: 2~5 years → 1.5~2 years

## PV resources & Future

- If 10% effc. on 0.1% earth's surface (= 500,000km<sup>2</sup>, or 1.3% of total desert area) → 100% world's current energy !
- If 10% effc. on 1.4% on UK land → 350 TWh/year (100% !)
- Production by Sharp: 123MW → 200MW
  - by BP Solar: 71MW, by Shell Solar: 55MW in 2002
  - others: Siemens Solar (joint venture with Shell)(doubling of world PV production every two years)
- Installation: over 200 GW by 2020,  
and 9000 TWh output by 2040 (over ¼ of global electricity demand)